**Product data sheet** 

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Ultra low Q<sub>G</sub> and Q<sub>GD</sub> for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery
- · Low spiking and ringing for low EMI designs
- MLPAK33 package (3.3 x 3.3 mm footprint)

### 3. Applications

- DC to DC conversion
- · Battery management
- Low-side load switch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	21.5	Α
Static charac	teristics						·
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 12.7 A; T <sub>j</sub> = 25 °C		-	5.7	6.7	mΩ
re	resistance	$V_{GS}$ = 4.5 V; $I_D$ = 11.2 A; $T_j$ = 25 °C		-	6.9	8.6	mΩ
Dynamic cha	racteristics					·	·
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; $I_{D}$ = 11.2 A; $V_{GS}$ = 4.5 V; $T_{j}$ = 25 °C		-	7.9	11.9	nC

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	D
2	S	source		
3	S	source		G—(FA)
4	G	gate	l h d	mbb076 S
5	D	drain		
6	D	drain		
7	D	drain	MLPAK33 (SOT8002-1)	
8	D	drain		

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package							
	Name	Description	Version					
PXN6R7-30QL	MLPAK33	plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1					

# 7. Marking

### Table 4. Marking codes

Type number	Marking code
PXN6R7-30QL	9AF

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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
gate-source voltage			-20	20	V
drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	21.5	Α
	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	12.7	Α
	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	8	Α
	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	62	Α
peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	87	Α
total power dissipation	T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	4.8	W
	T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
	T <sub>sp</sub> = 25 °C		-	40.3	W
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
diode		'	<u> </u>		
source current	T <sub>amb</sub> = 25 °C	[1]	-	1.5	Α
gedness			'	'	,
non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 2.3 A; DUT in avalanche (unclamped)		-	34.5	mJ
	drain-source voltage gate-source voltage drain current  peak drain current total power dissipation  junction temperature ambient temperature storage temperature diode source current gedness non-repetitive drain-	$ \begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \text{drain current} \\ \end{array} \begin{array}{c} V_{GS} = 10 \text{ V}; \ T_{amb} = 25 \text{ °C}; \ t \leq 5 \text{ s} \\ \hline V_{GS} = 10 \text{ V}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{GS} = 10 \text{ V}; \ T_{amb} = 100 \text{ °C} \\ \hline V_{GS} = 10 \text{ V}; \ T_{sp} = 25 \text{ °C} \\ \hline V_{GS} = 10 \text{ V}; \ T_{sp} = 25 \text{ °C} \\ \hline V_{GS} = 10 \text{ V}; \ T_{sp} = 25 \text{ °C} \\ \hline V_{GS} = 10 \text{ V}; \ T_{sp} = 25 \text{ °C} \\ \hline V_{amb} = 25 \text{ °C}; \ single pulse}; \ t_p \leq 10 \text{ µs} \\ \hline V_{amb} = 25 \text{ °C}; \ t \leq 5 \text{ s} \\ \hline V_{amb} = 25 \text{ °C} \\ \hline$	$ \begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \text{drain current} \\ \\ \end{array} \begin{array}{c} V_{GS} = 10 \text{ V}; \ T_{amb} = 25 \text{ °C}; \ t \leq 5 \text{ s} \\ \hline V_{GS} = 10 \text{ V}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{GS} = 10 \text{ V}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{GS} = 10 \text{ V}; \ T_{amb} = 100 \text{ °C} \\ \hline V_{GS} = 10 \text{ V}; \ T_{sp} = 25 \text{ °C} \\ \hline \end{array} $ $ \begin{array}{c} \text{peak drain current} \\ \text{total power dissipation} \\ \hline \end{array} \begin{array}{c} T_{amb} = 25 \text{ °C}; \ \text{single pulse}; \ t_p \leq 10 \text{ µs} \\ \hline T_{amb} = 25 \text{ °C}; \ \text{single pulse}; \ t_p \leq 10 \text{ µs} \\ \hline T_{amb} = 25 \text{ °C} \\ \hline \end{array} \begin{array}{c} \text{[1]} \\ \hline T_{amb} = 25 \text{ °C} \\ \hline \end{array} \begin{array}{c} \text{[1]} \\ \hline \end{array} $ $ \begin{array}{c} T_{amb} = 25 \text{ °C} \\ \hline \end{array} \begin{array}{c} \text{[1]} \\ \hline \end{array} $ $ \begin{array}{c} T_{amb} = 25 \text{ °C} \\ \hline \end{array} \begin{array}{c} \text{[1]} \\ \hline \end{array} $ $ \begin{array}{c} T_{amb} = 25 \text{ °C} \\ \hline \end{array} \begin{array}{c} \text{[1]} \\ \hline \end{array} $ $ \begin{array}{c} T_{amb} = 25 \text{ °C} \\ \hline \end{array} \begin{array}{c} \text{[1]} \\ \hline \end{array} $ $ \begin{array}{c} T_{amb} = 25 \text{ °C} \\ \hline \end{array} \begin{array}{c} \text{[1]} \\ \hline \end{array} \begin{array}{c} T_{amb} = 25 \text{ °C} \\ \hline \end{array} \begin{array}{c} \text{[1]} \\ \hline \end{array} \begin{array}{c} T_{amb} = 25 \text{ °C} \\ \hline \end{array} \begin{array}{c} T$	$ \begin{array}{c} drain\text{-source voltage} \\ drain\text{-source voltage} \\ \end{array} \begin{array}{c} T_j = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} -20 \\ \\ & -20 \\ \end{array} \\ \\ drain \text{ current} \\ \end{array} \begin{array}{c} V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C}; \ t \le 5 \ \text{s} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C} \\ \end{array} \begin{array}{c} [1] \\ -V_{GS} = 10 \ ^\vee\text{C}, \ T_{amb} = 25 \ ^\circ\text{C}, \ T_{amb} = 25 \ ^\circC$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

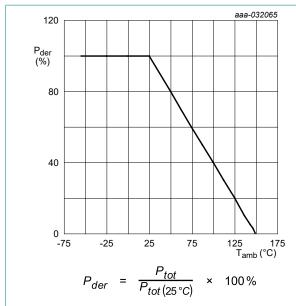


Fig. 1. Normalized total power dissipation as a function of ambient temperature

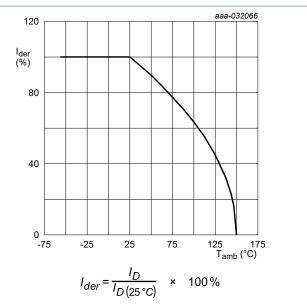


Fig. 2. Normalized continous drain current as a function of ambient temperature

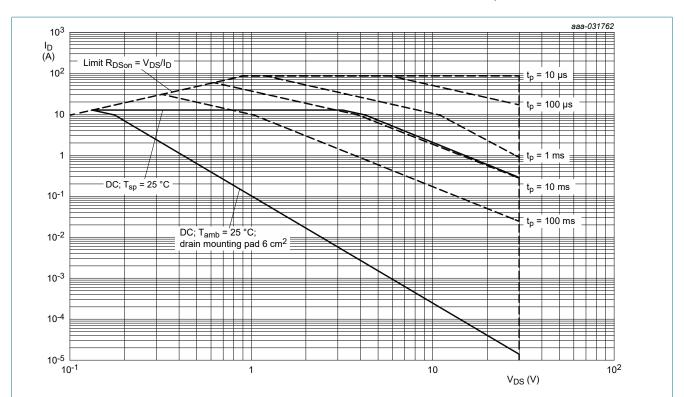


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

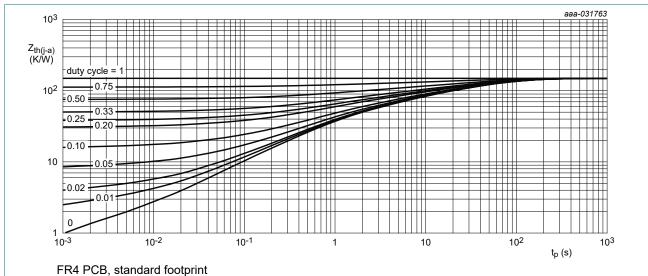
30 V, N-channel Trench MOSFET

### 9. Thermal characteristics

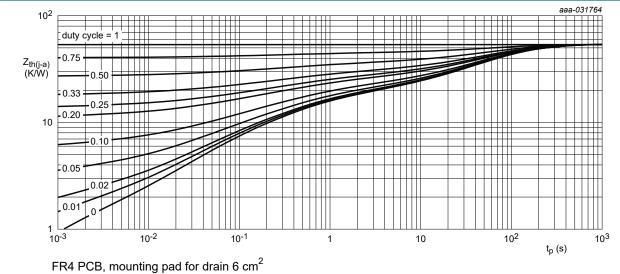
**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	150	190	K/W
	junction to ambient		[2]	-	60	75	K/W
		in free air; t ≤ 5 s	[2]	-	21	26	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	2.1	3.1	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 4.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, N-channel Trench MOSFET

# 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		l			
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.2	1.7	2.2	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 12.7 \text{ A}; T_j = 25 \text{ °C}$	-	5.7	6.7	mΩ
20011	resistance	$V_{GS} = 10 \text{ V}; I_D = 12.7 \text{ A}; T_j = 150 \text{ °C}$	-	8.8	10.4	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 11.2 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	6.9	8.6	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 12.7 \text{ A}; T_j = 25 \text{ °C}$	-	33	-	S
$R_G$	gate resistance	f = 1 MHz	-	1.2	-	Ω
Dynamic ch	naracteristics				'	
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; $I_{D}$ = 12.7 A; $V_{GS}$ = 10 V; $I_{j}$ = 25 °C	-	16.5	24.8	nC
		V <sub>DS</sub> = 15 V; I <sub>D</sub> = 11.2 A; V <sub>GS</sub> = 4.5 V;	-	7.9	11.9	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	2.8	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge		-	1.7	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	1.1	-	nC
Q <sub>GD</sub>	gate-drain charge	1	-	2.1	-	nC
$V_{GSpl}$	gate-source plateau voltage	$V_{DS} = 15 \text{ V}; I_D = 11.2 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	2.6	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	1150	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	380	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	66	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 11.2 A; V <sub>GS</sub> = 4.5 V;	-	5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$	-	8	-	ns
$t_{d(off)}$	turn-off delay time	1	-	6	-	ns
t <sub>f</sub>	fall time	1	-	3	-	ns
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.7	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 1.5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	15	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 4.5 \text{ V}; V_{DS} = 15 \text{ V}; T_j = 25 \text{ °C}$	-	6	-	nC
t <sub>a</sub>	reverse recovery rise time		-	8	-	ns
t <sub>b</sub>	reverse recovery fall time	1	-	7	-	ns

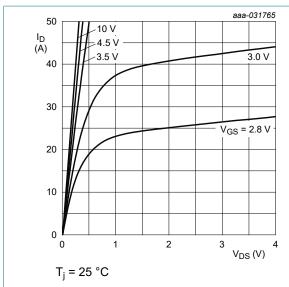


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

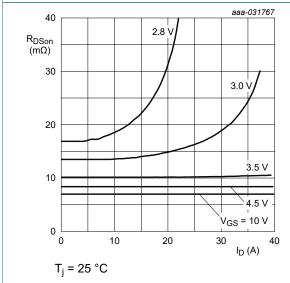


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

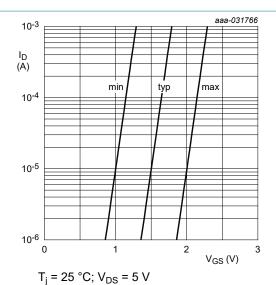


Fig. 7. Subthreshold drain current as a function of gate-source voltage

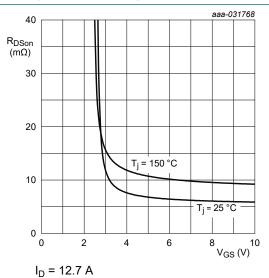


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

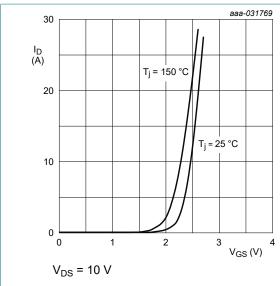


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

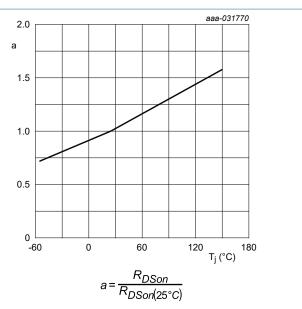


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

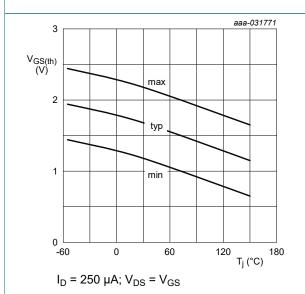
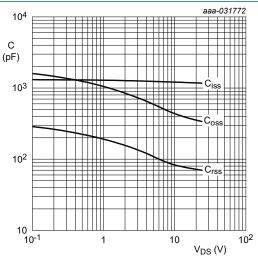


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

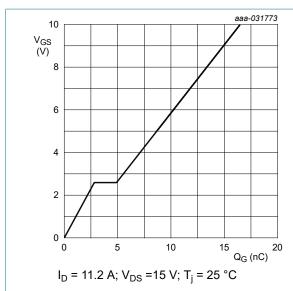


Fig. 14. Gate-source voltage as a function of gate charge; typical values

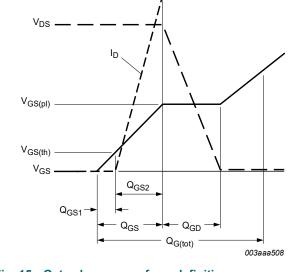


Fig. 15. Gate charge waveform definitions

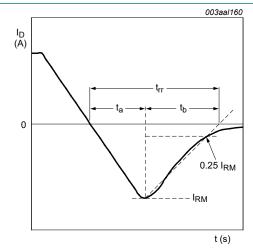


Fig. 16. Reverse recovery timing definition

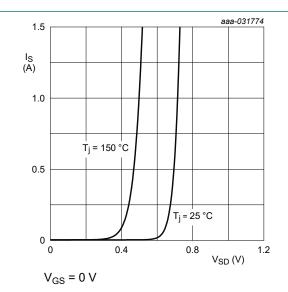
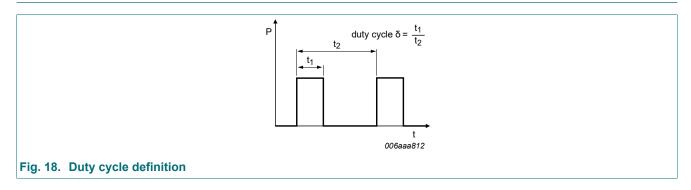


Fig. 17. Source current as a function of source-drain voltage; typical values

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# 11. Test information



30 V, N-channel Trench MOSFET

# 12. Package outline

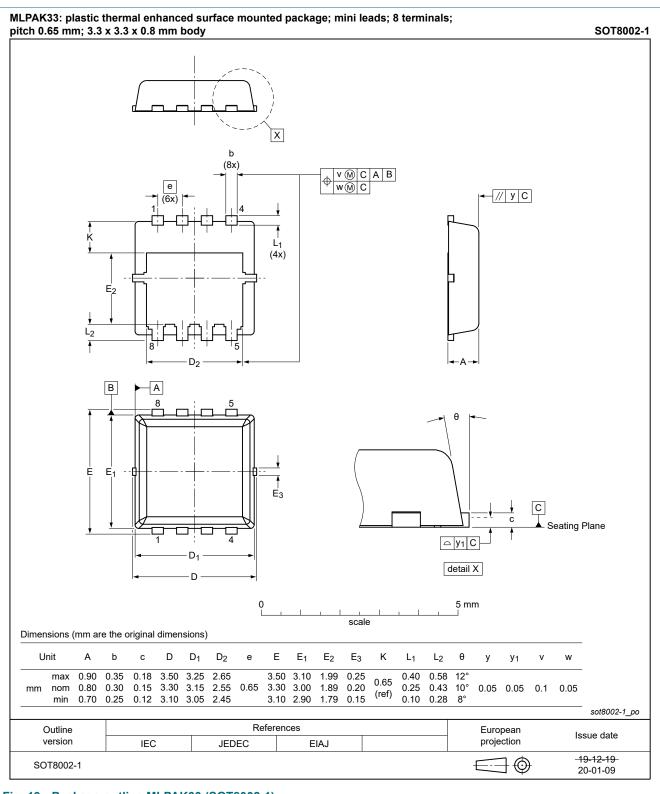
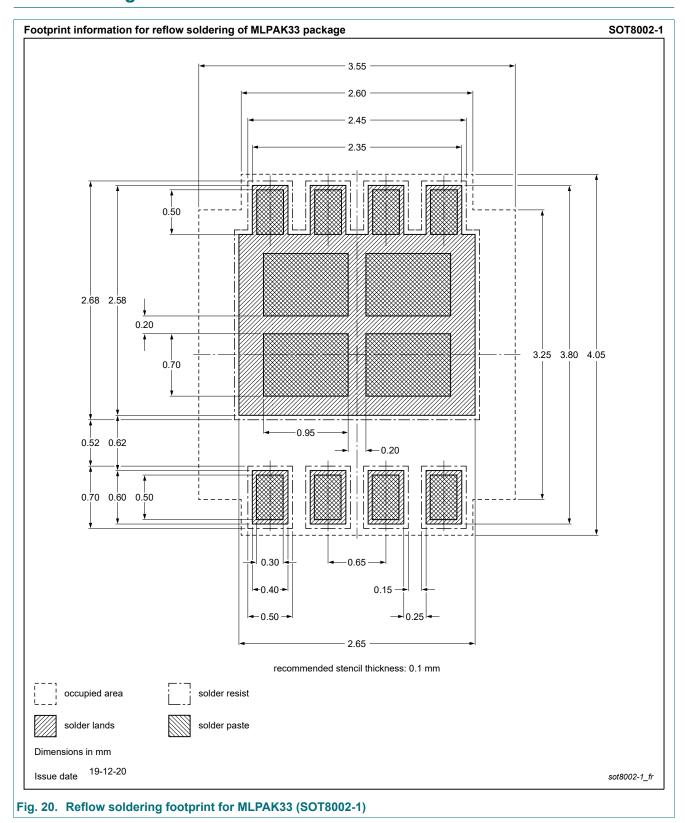


Fig. 19. Package outline MLPAK33 (SOT8002-1)

30 V, N-channel Trench MOSFET

# 13. Soldering



12 / 15

30 V, N-channel Trench MOSFET

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PXN6R7-30QL v.1	20201102	Product data sheet	-	-

#### 30 V, N-channel Trench MOSFET

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- 2] The term 'short data sheet' is explained in section "Definitions".
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### 30 V, N-channel Trench MOSFET

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